Katsumi Kishino

List of Publications by Year
in descending order

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153	4,228	159585 30	133252 59
papers	citations	h-index	g-index

155	155	155	2111
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Monolithically integrated green-to-orange color InGaN-based nanocolumn photonic crystal LEDs with directional radiation beam profiles. Applied Physics Express, 2022, 15, 022013.	2.4	6
2	Photonic band characterization in InGaN/GaN nanocolumn arrays with triangular and honeycomb lattices by angle-resolved micro-photoluminescence measurements. Japanese Journal of Applied Physics, 2021, 60, 060904.	1.5	4
3	Graphene-Based Transparent Conducting Substrates for GaN/AlGaN Nanocolumn Flip-Chip Ultraviolet Light-Emitting Diodes. ACS Applied Nano Materials, 2021, 4, 9653-9664.	5.0	6
4	Comparison of surface plasmon polariton characteristics of Ag- and Au-based InGaN/GaN nanocolumn plasmonic crystals. Applied Physics Express, 2021, 14, 105002.	2.4	1
5	Energy diagram and parameters regarding localized states in InGaN/GaN nanocolumns. Journal of Applied Physics, 2021, 130, .	2.5	4
6	Redâ€Emitting InGaNâ€Based Nanocolumn Lightâ€Emitting Diodes with Highly Directional Beam Profiles. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900771.	1.8	6
7	Two-dimensional multicolor (RGBY) integrated nanocolumn micro-LEDs as a fundamental technology of micro-LED display. Applied Physics Express, 2020, 13, 014003.	2.4	59
8	Carrier density dependence of localized carrier recombination dynamics in orange-emitting InGaN/GaN nanocolumns. Journal of Applied Physics, 2020, 128, 133102.	2.5	3
9	The influence of AlN buffer layer on the growth of self-assembled GaN nanocolumns on graphene. Scientific Reports, 2020, 10, 853.	3.3	8
10	GaN/AlGaN Nanocolumn Ultraviolet Light-Emitting Diode Using Double-Layer Graphene as Substrate and Transparent Electrode. Nano Letters, 2019, 19, 1649-1658.	9.1	39
11	Fabrication and optical properties of regularly arranged GaN-based nanocolumns on Si substrate. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, 031207.	1.2	9
12	Column diameter dependence of the strain relaxation effect in GaN/AlGaN quantum wells on GaN nanocolumn arrays. Applied Physics Express, 2019, 12, 125001.	2.4	9
13	Vertical GaN nanocolumns grown on graphene intermediated with a thin AlN buffer layer. Nanotechnology, 2019, 30, 015604.	2.6	21
14	Selective area growth of InGaN-based nanocolumn LED crystals on AlN/Si substrates useful for integrated Î¼-LED fabrication. Applied Physics Letters, 2018, 112, .	3.3	23
15	Effects of Introduction of InGaN Quantum Structures on Structural and Optical Properties of InGaN Nanocolumns. Physica Status Solidi (B): Basic Research, 2018, 255, 1700481.	1.5	1
16	Self-Organized Eu-Doped GaN Nanocolumn Light-Emitting Diode Grown by RF-Molecular-Beam Epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2018, 216, 1800501.	1.8	11
17	Effect of structural properties on optical characteristics of InGaN/GaN nanocolumns fabricated by selective-area growth. Applied Physics Express, 2017, 10, 045001.	2.4	4
18	Enhancement of light emission and internal quantum efficiency in orange and red regions for regularly arrayed InGaN/GaN nanocolumns due to surface plasmon coupling. Applied Physics Letters, 2017, 111, .	3.3	9

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19	Growth study of self-assembled GaN nanocolumns on silica glass by plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 2017, 480, 67-73.	1.5	19
20	Surface Phonons Studied by Raman Scattering in GaN Nanostructures. Journal of the Physical Society of Japan, 2017, 86, 074602.	1.6	8
21	Stableâ€wavelength operation of europiumâ€doped GaN nanocolumn lightâ€emitting diodes grown by rfâ€plasmaâ€assisted molecular beam epitaxy. Electronics Letters, 2017, 53, 666-668.	1.0	6
22	Independent drive of integrated multicolor (RGBY) micro-LED array using regularly arrayed InGaN based nanocolumns. , 2017, , .		2
23	Investigation of yellow/green II-VI compound semiconductor laser diode structures on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 669-672.	0.8	3
24	Spatial emission distribution and carrier recombination dynamics in regularly arrayed InGaN/GaN quantum structure nanocolumns. Japanese Journal of Applied Physics, 2016, 55, 105001.	1.5	4
25	Influence of GaN column diameter on structural properties for InGaN nanocolumns grown on top of GaN nanocolumns. AIP Advances, 2016, 6, .	1.3	16
26	Spectrally-broadened multimode lasing based on structurally graded InGaN nanocolumn photonic crystals suitable for reduction of speckle contrast. Applied Physics Letters, 2016, 109, .	3.3	10
27	Self-organization of dislocation-free, high-density, vertically aligned GaN nanocolumns involving InGaN quantum wells on graphene/SiO₂covered with a thin AlN buffer layer. Nanotechnology, 2016, 27, 055302.	2.6	22
28	Crystal structure and optical properties of a high-density InGaN nanoumbrella array as a white light source without phosphors. NPG Asia Materials, 2016, 8, e289-e289.	7.9	6
29	Photon correlation study of background suppressed single InGaN nanocolumns. Japanese Journal of Applied Physics, 2016, 55, 04EK03.	1.5	7
30	Periodic Radiation Patterns and Circulating Direction of Lasing Light by Quasi Whispering Gallery Mode in Hexagonal GaN Microdisk. Journal of the Physical Society of Japan, 2016, 85, 053401.	1.6	2
31	Application of indium tin oxide to the pâ€cladding layers of yellow/green IIâ€VI compound semiconductor laser diode structures on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 665-668.	0.8	0
32	Carrier-density dependence of photoluminescence from localized states in InGaN/GaN quantum wells in nanocolumns and a thin film. Journal of Applied Physics, 2015, 118, .	2.5	17
33	GaN nanocolumn arrays with diameter <30Ânm prepared by twoâ€step selective area growth. Electronics Letters, 2015, 51, 2125-2126.	1.0	19
34	Selective-area growth of GaN nanocolumns on Si(111) substrates for application to nanocolumn emitters with systematic analysis of dislocation filtering effect of nanocolumns. Nanotechnology, 2015, 26, 225602.	2.6	130
35	Thermally Engineered Flip-Chip InGaN/GaN Well-Ordered Nanocolumn Array LEDs. IEEE Photonics Technology Letters, 2015, 27, 2343-2346.	2.5	6
36	Flipâ€chip bonding and fabrication of wellâ€ordered nanocolumn arrays on sputterâ€deposited AlN/Si (111) substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 992-996.	1.8	7

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37	Investigation of p-side contact layers for IIâ€“VI compound semiconductor optical devices fabricated on InP substrates by MBE. Journal of Crystal Growth, 2015, 425, 199-202.	1.5	5
38	Monolithic integration of fourâ€colour InGaNâ€based nanocolumn LEDs. Electronics Letters, 2015, 51, 852-854.	1.0	61
39	Switching of whispering gallery mode in hexagonal GaN microdisk by change in condition of reflection surface. Electronics Letters, 2015, 51, 170-172.	1.0	1
40	Novel selective area growth (SAG) method for regularly arranged AlGaN nanocolumns using nanotemplates. Journal of Crystal Growth, 2015, 425, 316-321.	1.5	25
41	Optical properties of arrays of hexagonal GaN microdisks acting as whisperingâ€galleryâ€modeâ€type optical microcavities. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1017-1020.	1.8	4
42	Directional radiation beam from yellow-emitting InGaN-based nanocolumn LEDs with ordered bottom-up nanocolumn array. Applied Physics Express, 2014, 7, 112102.	2.4	37
43	Investigation of p-contact layers for BeZnSeTe/MgZnCdSe optical devices on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1273-1277.	0.8	2
44	Wideâ€range visible luminescence of ZnCdSe/BeZnTe typeâ€II superlattices grown on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1213-1217.	0.8	1
45	Formation of indium tin oxide transparent electrodes by magnetron sputtering for II-VI compound semiconductor optical devices on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1278-1281.	0.8	0
46	Green-Light Nanocolumn Light Emitting Diodes With Triangular-Lattice Uniform Arrays of InGaN-Based Nanocolumns. IEEE Journal of Quantum Electronics, 2014, 50, 538-547.	1.9	37
47	Monolithic Integration of InGaN-Based Nanocolumn Light-Emitting Diodes with Different Emission Colors. Applied Physics Express, 2013, 6, 012101.	2.4	116
48	Complex strain distribution in individual facetted InGaN/GaN nano-columnar heterostructures. Optical Materials Express, 2013, 3, 47.	3.0	9
49	Fundamental optical properties of InN grown by epitaxial lateral overgrowth method. , 2013, , .		2
50	Raman scattering from surface phonons in GaN nanostructures. , 2013, , .		1
51	Photoluminescence Behaviors of Orange-Light-Emitting InGaN-Based Nanocolumns Exhibiting High Internal Quantum Efficiency (17â€“22%). Japanese Journal of Applied Physics, 2013, 52, 08JD09.	1.5	16
52	633 nm Red Emissions from InGaN Nanocolumn Light-Emitting Diode by Radio Frequency Plasma Assisted Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JE18.	1.5	25
53	Confinement of Optical Phonons Observed by Raman Scattering in GaN/AlN Multiple Quantum Disk Nanocolumns. Journal of the Physical Society of Japan, 2013, 82, 014604.	1.6	8
54	Twoâ€photon absorption induced antiâ€Stokes emission in single InGaN/GAN quantumâ€dotâ€like objects. Physica Status Solidi - Rapid Research Letters, 2013, 7, 344-347.	2.4	2

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55	Well-arranged novel InGaN hexagonal nanoplates at the tops of nitrogen-polarity GaN nanocolumn arrays. AIP Advances, 2012, 2, .	1.3	13
56	Optical properties of InGaN/GaN nanocolumns in yellowâ€toâ€red region. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2477-2480.	0.8	4
57	Photoluminescence properties of selectively grown InN microcrystals. Physica Status Solidi - Rapid Research Letters, 2012, 6, 157-159.	2.4	8
58	Lowâ€temperature photoluminescence studies of Inâ€rich InAlN nanocolumns. Physica Status Solidi - Rapid Research Letters, 2012, 6, 123-125.	2.4	10
59	Breakdown of the Selection Rule of Raman Spectra in a Single GaN Nanocolumn. E-Journal of Surface Science and Nanotechnology, 2012, 10, 321-324.	0.4	3
60	Electric Conduction in a Single GaN Nanocolumn. E-Journal of Surface Science and Nanotechnology, 2012, 10, 355-359.	0.4	0
61	Raman Scattering from a Surface Phonon in GaN Nanowalls and Regularly-Arrayed GaN Nanocolumns. , 2011, , .		1
62	Epitaxial lateral overgrowth of InN by rf-plasma-assisted molecular-beam epitaxy. AIP Advances, 2011, 1, 042145.	1.3	8
63	Optically Pumped Green (530â€“560 nm) Stimulated Emissions from InGaN/GaN Multiple-Quantum-Well Triangular-Lattice Nanocolumn Arrays. Applied Physics Express, 2011, 4, 055001.	2.4	42
64	Whispering gallery mode in periodic InGaNâ€based hexagonal nanoring arrays grown by rfâ€MBE using Tiâ€mask selectiveâ€area growth. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 37-40.	1.8	6
65	Formation of InGaN quantum dots in regularly arranged GaN nanocolumns grown by rfâ€plasmaâ€assisted molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2374-2377.	0.8	18
66	Dislocation reduction via selective-area growth of InN accompanied by lateral growth by rf-plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2010, 97, .	3.3	40
67	Strain relaxation effect by nanotexturing InGaN/GaN multiple quantum well. Journal of Applied Physics, 2010, 107, .	2.5	93
68	Emission color control from blue to red with nanocolumn diameter of InGaN/GaN nanocolumn arrays grown on same substrate. Applied Physics Letters, 2010, 96, .	3.3	359
69	Optical properties of InGaN/GaN nanopillars fabricated by postgrowth chemically assisted ion beam etching. Journal of Applied Physics, 2010, 107, .	2.5	88
70	Lasing Actions in GaN Tiny Hexagonal Nanoring Resonators. IEEE Photonics Journal, 2010, 2, 1027-1033.	2.0	16
71	Energy- and density-dependent dynamics of photoexcited carriers in InN films. Applied Physics Letters, 2009, 95, .	3.3	4
72	Positive binding energy of a biexciton confined in a localization center formed in a single<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mi>x</mml:mi></mml:msub> disk. Physical Review B, 2009, 79, .	3.3	38

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73	Exciton and biexciton properties in GaN nanocolumn: dependence on morphology and diameter. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 141-143.	0.8	1
74	Tiâ€mask selectiveâ€area growth of GaN nanorings by RFâ€plasmaâ€assisted molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S607.	0.8	3
75	Improved Ti-mask selective-area growth (SAG) by rf-plasma-assisted molecular beam epitaxy demonstrating extremely uniform GaN nanocolumn arrays. Journal of Crystal Growth, 2009, 311, 2063-2068.	1.5	254
76	Photopumped green lasing on BeZnSeTe double heterostructures grown on InP substrates. Applied Physics Letters, 2009, 94, 021104.	3.3	19
77	Selective growth of GaN nanocolumns on predeposited Al patterns by rf-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1879-1882.	0.8	3
78	Effect of Be-doping on InGaN/GaN nanocolumn light-emitting diode structures by rf-plasma-assisted molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 3069-3072.	0.8	6
79	Ultraviolet GaNâ€based nanocolumn lightâ€emitting diodes grown on nâ€(111) Si substrates by rfâ€plasmaâ€assisted molecular beam epitaxy. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 1067-1069.	1.8	40
80	Proposal of BeZnSeTe/MgZnCdSe II–VI compound semiconductors on InP substrates for green laser diodes. , 2008, , .		1
81	Growth and properties of InAlN nanocolumns emitting in optical communication wavelengths. , 2008, , .		0
82	Selective-Area Growth of GaN Nanocolumns on Si(111) Substrates Using Nitrided Al Nanopatterns by RF-Plasma-Assisted Molecular-Beam Epitaxy. Applied Physics Express, 2008, 1, 015006.	2.4	37
83	GaN/AlGaN nanocolumn ultraviolet light-emitting diodes grown on n-(111) Si by RF-plasma-assisted molecular beam epitaxy. Electronics Letters, 2008, 44, 151.	1.0	63
84	Lattice parameters, deviations from Vegardâ€™s rule, and E2 phonons in InAlN. Applied Physics Letters, 2008, 93, .	3.3	44
85	InGaN/GaN nanocolumn LEDs emitting from blue to red. , 2007, , .		94
86	Ultrafast Intersubband Relaxation Dynamics and Coherent Nonlinearity in Bulk and Waveguide structures of GaN/AlN Multiple Quantum Wells. AIP Conference Proceedings, 2007, , .	0.4	0
87	Structural and optical properties of GaN nanocolumns grown on (0001) sapphire substrates by rf-plasma-assisted molecular-beam epitaxy. Journal of Crystal Growth, 2007, 300, 259-262.	1.5	80
88	Selective growth of GaN nanocolumns by Al thin layer on substrate. Physica Status Solidi (B): Basic Research, 2007, 244, 1815-1819.	1.5	29
89	Raman Scattering in GaN/AlN Multiple Quantum Disk Nanocolumns. AIP Conference Proceedings, 2007, , .	0.4	0
90	Origin of high oscillator strength in green-emitting InGaNâ•GaN nanocolumns. Applied Physics Letters, 2006, 89, 163124.	3.3	92

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91	High p-type doping level of MgZnCdSe on InP substrates by inserting ZnTe thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 857-860.	0.8	3
92	Long life operations over 5000 hours of BeZnSeTe/MgZnCdSe visible light emitting diodes on InP substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 924-928.	1.5	14
93	Yellowâ€“green lasing operations of ZnCdTe/MgZnSeTe laser diodes on ZnTe substrates. Physica Status Solidi (B): Basic Research, 2006, 243, 955-958.	1.5	5
94	Growth of high-In-content InGaN multiple quantum disk nanocolumns on Si(111) by RF plasma-assisted molecular-beam epitaxy. Physica Status Solidi (B): Basic Research, 2006, 243, 1481-1485.	1.5	6
95	High structural quality InNâ•In0.75Ga0.25N multiple quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2006, 89, 041907.	3.3	26
96	Raman Scattering in GaN Nanocolumns and GaN/AlN Multiple Quantum Disk Nanocolumns. E-Journal of Surface Science and Nanotechnology, 2006, 4, 227-232.	0.4	11
97	Room temperature operation of 1.55.MU.m wavelength-range GaN/AlN quantum well intersubband photodetectors. IEICE Electronics Express, 2005, 2, 566-571.	0.8	7
98	All-optical modulation using intersubband transitions at 1.55 Î¼m in GaN/AlN multiple quantum well. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2748-2752.	0.8	1
99	Highly efficient blue to red emissions of InGaN/GaN nano-disks integrated into GaN nanocolumns. , 2005, , .		1
100	Lasing operation of ZnTe based yellow-green laser diodes. , 2005, , .		1
101	Non-Polar GaN/AlN Superlattices on A-plane AlN (500nm) Buffer Layers Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2004, 831, 212.	0.1	0
102	Self-Organized GaN/AlN Superlattice Nanocolumn Crystals Grown by RF-MBE. Materials Research Society Symposia Proceedings, 2004, 831, 666.	0.1	3
103	Aging characteristics of IIâ€“VI yellow light emitting diodes with beryllium chalcogenide (BeZnSeTe) active layers on InP substrates. Physica Status Solidi A, 2004, 201, 2708-2711.	1.7	7
104	Growth and characterization of InGaN double heterostructures for optical devices at 1.5â€“1.7 mm communication wavelengths. Physica Status Solidi A, 2004, 201, 2850-2854.	1.7	9
105	Development of yellow-green LEDs and LDs using MgZnCdSe-BeZnTe superlattices on InP substrates by MBE. Physica Status Solidi (B): Basic Research, 2004, 241, 739-746.	1.5	6
106	Characterization of ZnCdSeTe/MgZnSeTe materials for ZnTe-based visible optical devices. Physica Status Solidi (B): Basic Research, 2004, 241, 483-486.	1.5	14
107	Proposal of a novel BeZnSeTe quaternary for II-VI middle range visible light emitting devices on InP substrates. Physica Status Solidi (B): Basic Research, 2004, 241, 747-750.	1.5	11
108	Stimulated emission from GaN nanocolumns. Physica Status Solidi (B): Basic Research, 2004, 241, 2754-2758.	1.5	52

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109	Yellow-green emitters based on beryllium-chalcogenides on InP substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1477-1486.	0.8	9
110	InGaN/GaN Multiple Quantum Disk Nanocolumn Light-Emitting Diodes Grown on (111) Si Substrate. Japanese Journal of Applied Physics, 2004, 43, L1524-L1526.	1.5	351
111	Ultrafast intersubband relaxation and nonlinear susceptibility at 1.55â€‚Î¼m in GaN/AlN multiple-quantum wells. Applied Physics Letters, 2004, 84, 1102-1104.	3.3	91
112	Yellow-green ZnCdSe/BeZnTe II-VI laser diodes grown on InP substrates. Applied Physics Letters, 2002, 81, 972-974.	3.3	36
113	Reduction of Defect Density of ZnCdSe on InP Substrates by Introducing BeZnTe Buffer Layers. Physica Status Solidi (B): Basic Research, 2002, 229, 107-110.	1.5	5
114	Visible Light Emitting Diode with ZnCdSe/BeZnTe Superlattices as an Active Layer and MgSe/BeZnTe Superlattices as a p-Cladding Layer. Physica Status Solidi (B): Basic Research, 2002, 229, 1001-1004.	1.5	24
115	Refractive Index Measurements of BeZnTe and Related Superlattices on InP and Application for Waveguide Analysis of MgZnCdSe/BeZnTe Visible Lasers. Physica Status Solidi (B): Basic Research, 2002, 229, 987-990.	1.5	9
116	ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 229, 991-994.	1.5	15
117	Intersubband Absorption at? ? 1.2-1.6 ?m in GaN/AlN Multiple Quantum Wells Grown by rf-Plasma Molecular Beam Epitaxy. Physica Status Solidi A, 2002, 192, 124-128.	1.7	7
118	MgZnCdSe/BeZnTe Visible Light-Emitting Diode with Longer Device Lifetime over 1000 h. Physica Status Solidi A, 2002, 192, 201-205.	1.7	6
119	Improved Responsivity of AlGaN-Based Resonant Cavity-Enhanced UV Photodetectors Grown on Sapphire by RF-MBE. Physica Status Solidi A, 2002, 192, 292-295.	1.7	10
120	Intersubband transition in (GaN)m/(AlN)n superlattices in the wavelength range from 1.08 to 1.61 Î¼m. Applied Physics Letters, 2002, 81, 1234-1236.	3.3	167
121	ZnCdTe/ZnTe Light Emitting Diodes with CdSe n-Type Contact Layers Grown on ZnTe Substrates by Molecular Beam Epitaxy. Physica Status Solidi (B): Basic Research, 2002, 229, 991-994.	1.5	1
122	AlGaN Resonant Tunneling Diodes Grown by rf-MBE. Physica Status Solidi A, 2001, 188, 187-190.	1.7	21
123	Resonant-Cavity-Enhanced UV Metal-Semiconductor-Metal (MSM) Photodetectors Based on AlGaN System. Physica Status Solidi A, 2001, 188, 321-324.	1.7	14
124	AlGaN Resonant Tunneling Diodes Grown by rf-MBE. Physica Status Solidi A, 2001, 188, 187-190.	1.7	1
125	Step Flow Surface Morphology in Plasma Assisted Molecular Beam Epitaxy Grown GaN. Materials Research Society Symposia Proceedings, 2000, 639, 3331.	0.1	0
126	Novel II-VI Light Emitting Diodes Fabricated on InP Substrates Applying Wide-Gap and Highly p-Dopable BeZnTe for p-Cladding Layers. Physica Status Solidi A, 2000, 180, 37-43.	1.7	9

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127	Suppression of Inversion Domains and Decrease of Threading Dislocations in Migration Enhanced Epitaxial GaN by RF-Molecular Beam Epitaxy. Physica Status Solidi A, 2000, 180, 65-71.	1.7	2
128	Self-organization of GaN/Al0.18Ga0.82N multi-layer nano-columns on (0001) Al2O3 by RF molecular beam epitaxy for fabricating GaN quantum disks. Journal of Crystal Growth, 1998, 189-190, 138-141.	1.5	96
129	High-speed GaN growth and compositional control of GaN-AlGaN superlattice quasi-ternary compounds by RF-radical source molecular beam epitaxy. IEEE Journal of Selected Topics in Quantum Electronics, 1998, 4, 550-556.	2.9	14
130	Refractive index measurements of MgZnCdSe IIâ€“VI compound semiconductors grown on InP substrates and fabrications of 500â€“600 nm range MgZnCdSe distributed Bragg reflectors. Journal of Applied Physics, 1997, 81, 7575-7579.	2.5	18
131	Growth of Self-Organized GaN Nanostructures on $f Al_{2}O_{3}(0001)$ by RF-Radical Source Molecular Beam Epitaxy. Japanese Journal of Applied Physics, 1997, 36, L459-L462.	1.5	341
132	Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. Journal of Electronic Materials, 1996, 25, 425-430.	2.2	35
133	Self-organization mechanism of GaInP quantum wires in (GaP) m /(InP) m short-period binary superlattices for GaInP/AlInP multi-quantum-wire (MQWR) lasers. Optical and Quantum Electronics, 1996, 28, 547-556.	3.3	7
134	Substrate Misorientation, Multiâ€Quantumâ€Barrier, and Thermal Annealing Effects in MgZnSSe and ZnCdSe Compounds and Blueâ€Green IIâ€VI Light Emitting Devices. Physica Status Solidi (B): Basic Research, 1995, 187, 327-335.	1.5	1
135	Research Trends and Prospects of Blue and Ultraviolet Laser Diodes.. The Review of Laser Engineering, 1995, 23, 487-496.	0.0	0
136	Refractive indices measurement of (GaInP)m/(AlInP)nquasiâ€quaternaries and GaInP/AlInP multiple quantum wells. Journal of Applied Physics, 1994, 76, 1809-1818.	2.5	40
137	600â€nm wavelength range GaInP/AlInP quasiâ€quaternary compounds and lasers prepared by gasâ€source molecularâ€beam epitaxy. Journal of Applied Physics, 1993, 74, 819-824.	2.5	25
138	Remarkable reduction of threshold current density by substrate misorientation effects in 660 nm visible light lasers with GaInP bulk active layers. Applied Physics Letters, 1992, 60, 1046-1048.	3.3	21
139	Enhanced carrier confinement effect by the multiquantum barrier in 660 nm GaInP/AlInP visible lasers. Applied Physics Letters, 1991, 58, 1822-1824.	3.3	80
140	Highâ€opticalâ€quality GaInP and GaInP/AlInP double heterostructure lasers grown on GaAs substrates by gasâ€source molecularâ€beam epitaxy. Journal of Applied Physics, 1989, 66, 4557-4559.	2.5	22
141	Fabrication and lasing characteristics of 0.67 µm GaInAsP/AlGaAs visible lasers prepared by liquid phase epitaxy on. IEEE Journal of Quantum Electronics, 1987, 23, 180-187.	1.9	13
142	Substrate Misorientation Effect On Cubic And Hexagonal GaN Grown On GaAs By Molecular Beam Epitaxy Using RF-radical Nitrogen Source. , 0, , .		0
143	Room temperature CW operation of GaInP/AlGaInP multiple quantum wire visible lasers (MQWR-LD). , 0, , .		2
144	Molecular beam epitaxial growth of MgZnCdSe on (100) InP substrates. , 0, , .		0

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145	Effect of (GaP)/sub m//(InP)/sub m/ short period binary superlattice period on quantum wire formation by strain induced lateral layer ordering in GaInP/AlInP multi-quantum-wire lasers. , 0, , .		0
146	Quasi-free standing GaN epitaxial layer grown on nano-columnar GaN by RF-plasma assisted molecular beam epitaxy. , 0, , .		0
147	Room temperature negative differential resistance in AlN/GaN double barrier resonant tunneling diodes grown by RF-plasma assisted molecular beam epitaxy. , 0, , .		2
148	Yellow-green lasing emission from ZnCdSe/BeZnTe II-VI laser diodes on InP substrates. , 0, , .		0
149	High-quality InN grown by RF-plasma assisted molecular beam epitaxy as novel materials for optical communication. , 0, , .		0
150	Ultrafast intersubband relaxation at 1.55 Î¼m in GaN/AlN MQWs. , 0, , .		0
151	Middle-range visible light emitting devices fabricated using BeZnSeTe/MgZnCdSe II-VI compounds on InP substrates. , 0, , .		0
152	Ultrafast intersubband relaxation dynamics in GaN/AlN multiple quantum wells using two-color pump-probe technique. , 0, , .		0
153	Ti-mask Selective-Area Growth of GaN by RF-Plasma-Assisted Molecular-Beam Epitaxy for Fabricating Regularly Arranged InGaN/GaN Nanocolumns. Applied Physics Express, 0, 1, 124002.	2.4	179